

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,085,616 B2
APPLICATION NO. : 09/917842
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INVENTOR(S) : Chin et al.

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 3, line 21, delete "processing such" and insert -- processing--such --, therefor.

In column 3, line 60, below "pulsed flow." insert -- Thereafter as indicated in step 370 of FIG. 3, alternating monolayers of each deposition gas are chemisorbed onto the surface of the semiconductor wafer to form a material layer having a desired thickness thereon. Each monolayer is chemisorbed onto the surface of the semiconductor wafer as the wafer support is alternately moved between the two or more deposition regions through aperture 250. --, as a new paragraph.

In column 4, line 10, in Claim 1, delete "a deposition" and insert -- a vacuum deposition --, therefor.

In column 4, line 14, in Claim 1, after "support is" insert -- vertically --.

In column 4, line 20, in Claim 3, delete "controls" and insert -- control --, therefor.

In column 5, line 38, in Claim 15, after "support" delete "on" and insert -- to --, therefor.

Signed and Sealed this

Seventeenth Day of April, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office